

A B S T R A C T

A developing method is used for subjecting a light-exposed resist film disposed on a wafer W to a developing process by a developing solution and a rinsing process by a rinsing liquid. In a state where the resist film on the wafer W is wet with the developing solution or rinsing liquid before a drying process is performed on the wafer W, a chemical liquid (curing chemical liquid), which contains a resist curing aid contributory to curing of a resist film remaining on the wafer W, is supplied onto a surface of the wafer W. Then, ultraviolet rays are radiated onto a surface of the wafer to cure a resist film remaining on the wafer W by a synergistic effect of the resist curing aid and the ultraviolet rays thus radiated, so as to prevent pattern fall.